

PHOTON-ASSISTED CHEMICAL ETCHING OF SILICON CARBIDE FILMS
FROM REACTION CHAMBER PARTS

ABSTRACT

5 The present invention relates to a method for etching a silicon carbide film from one
or more parts of a reaction chamber suitable for the deposition of silicon carbide layers on a
substrate. The method comprises the steps of: (i) providing a silicon carbide film on one or
more parts of a reaction chamber of a reactor for deposition silicon carbide; (ii) executing at
least one cycle of an etching process. The etching process includes at least one cycle of a
10 UV-photon assisted chemical etching. The present invention further relates to a reactor
adapted to execute said method.

(FIG. 1)